

TIP35CW TIP36CW

Complementary Silicon High Power Transistors

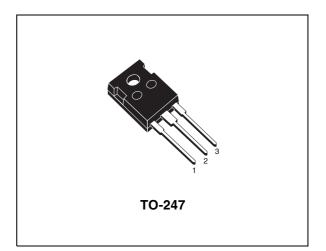
Features

 STMicroelectronics PREFERRED SALESTYPES

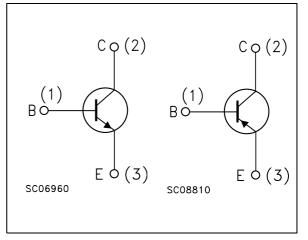
Description

The device is a silicon Epitaxial-Base NPN transistor mounted in TO-247 plastic package. It is intentend for use in power amplifier and switching applications.

The complementary PNP type is TIP36CW.



Internal Schematic Diagram



Order Codes

Part Number	Marking	Package	Packing
TIP35CW	TIP35C W	TO-247	Tube
TIP36CW	TIP36C W	TO-247	Tube

rev.2

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1 Absolute Maximum Ratings

Symbol	Parameter		Value	Unit
	NPN		TIP35CW	
		PNP	TIP36CW	
V _{CBO}	Collector-Base Voltage (I _E = 0)		100	V
V _{CEO}	Collector-Emitter Voltage (I _B = 0)		100	V
V _{EBO}	Emitter-Base Voltage (I _C = 0)		5	V
۱ _C	Collector Current		25	А
I _{CM}	Collector Peak Current (t _p < 5ms)		50	А
I _B	Base Current		5	А
P _{tot}	Total Dissipation at $T_c = 25^{\circ}C$		125	W
T _{stg}	Storage Temperature	-65 to 150	°C	
TJ	Max. Operating Junction Temperature	150	°C	

Note: For PNP types voltage and current values are negative.

Table 2.Thermal Data

Symbol	Parameter	Value	Unit
R _{thj-case}	Thermal Resistance Junction-Case Max	1	°C/W

2 Electrical Characteristics

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
I _{CEO}	Collector Cut-off Current $(I_B = 0)$	V _{CE} = 60 V			1	mA
I _{EBO}	Emitter Cut-off Current $(I_{C} = 0)$	V _{EB} = 5 V			1	mA
I _{CES}	Collector Cut-off Current (V _{BE} = 0)	V _{CE} = Rated V _{CEO}			0.7	mA
V _{CEO(SUS)} Note: 1	Collector-Emitter Sustaining Voltage (I _B = 0)	I _C = 30 mA	100			V
h _{FE} Note: 1	DC Current Gain	$I_{C} = 1.5 A$ $V_{CE} = 4 V$ $I_{C} = 15 A$ $V_{CE} = 4 V$	25 10		50	
V _{CE(sat)} Note: 1	Collector-Emitter Saturation Voltage	$I_{C} = 15 A$ $I_{B} = 1.5 A$ $I_{C} = 25 A$ $I_{B} = 5 A$			1.8 4	V V
V _{BE(on)} Note: 1	Base-Emitter Voltage	$I_{C} = 15 \text{ A} \qquad V_{CE} = 4 \text{ V}$ $I_{C} = 25 \text{ A} \qquad V_{CE} = 4 \text{ V}$			2 4	V V
f _T	Transition Frequency	$I_C = 1 A$ $V_{CE} = 10 V f = 1 MHz$	3			MHz
h _{fe}	Small Signall Current Gain	I _C = 1 A V _{CE} = 10 V f = 1 MHz	25			

Table 3.Electrical Characteristics ($T_{case} = 25^{\circ}C$; unless otherwise specified)

Note: 1 Pulsed duration = $300 \ \mu s$, duty cycle $\le 1.5\%$.

2 For PNP types voltage and current values are negative.

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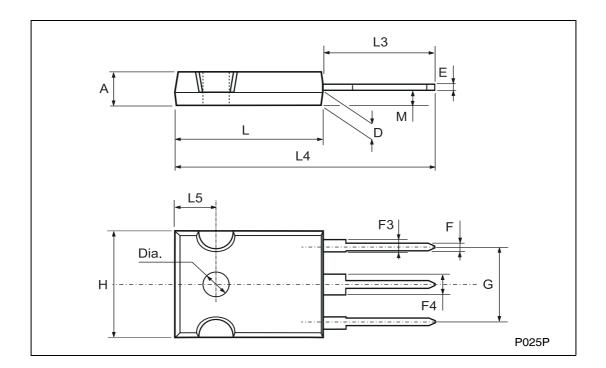
3 Package Mechanical Data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect . The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com



DIM.	DIM mi				inch	
DIN.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
А	4.7		5.3	0.185		0.209
D	2.2		2.6	0.087		0.102
E	0.4		0.8	0.016		0.031
F	1		1.4	0.039		0.055
F3	2		2.4	0.079		0.094
F4	3		3.4	0.118		0.134
G		10.9			0.429	
н	15.3		15.9	0.602		0.626
L	19.7		20.3	0.776		0.779
L3	14.2		14.8	0.559		0.582
L4		34.6			1.362	
L5		5.5			0.217	
М	2		3	0.079		0.118

TO-247 MECHANICAL DATA



4 Revision History

Date	Revision	Changes
02-Nov-2005	1	Initial release.
12-Dec-2005	2	Added the ECOPACK Label.



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